

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: Not yet assigned

Examiner: Not yet assigned

Serial No. Not yet assigned

Filed: December 28, 2001

In re Application of: Hawley et al.

For: METHOD FOR FABRICATING A MOS TRANSISTOR HAVING IMPROVED
TOTAL RADIATION-INDUCED LEAKAGE CURRENT

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on 12/28/01, Signed Stephanie Davis

PRELIMINARY AMENDMENT

Director of Patents
Box New Application
Washington, D.C. 20231

Dear Sir:

Kindly amend the above-identified application as follows.

In the Specification:

Page 1, Line 8, please delete "MOS TRANSISTOR HAVING IMPROVED TOTAL RADIATION-INDUCED LEAKAGE CURRENT AND METHOD FOR FABRICATING SAME" and insert --METHOD FOR FABRICATING A MOS TRANSISTOR HAVING IMPROVED TOTAL RADIATION-INDUCED LEAKAGE CURRENT--.

Page 1, Line 11, please insert -This application is a divisional of United States Patent Application Serial Number 09/741,949, filed December 20, 2000, entitled "MOS TRANSISTOR HAVING IMPROVED TOTAL RADIATION-INDUCED LEAKAGE CURRENT AND METHOD FOR FABRICATING SAME".-